

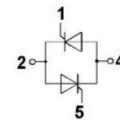
PRODUCT FEATURES

- Compact Design
- One screw mounting
- Heat transfer and isolation through DBC
- Glass passivation thyristor chips
- Low Leakage Current



APPLICATIONS

- Soft starters
- Temperature control
- Light control



ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Values	Unit
V _{RRM}	Maximum Repetitive Reverse Voltage	T _{vj} =125°C	800	V
V _{DRM}	Maximum repetitive peak off-state voltage			
V _{RSM}	Non-Repetitive Reverse Voltage	T _{vj} =125°C	900	V
V _{DSM}	Non-repetitive peak off-state voltage			
I _{RRM}	Maximum Repetitive Reverse Current	T _{vj} =125°C	5	mA
I _{DRM}	Maximum repetitive peak off-state Current			
I _{T(AV)}	Mean On-state Current	T _c =85°C	55	A
I _{T(RMS)}	RMS Current	T _c =85°C, sin180°	80	
I _{TSM}	Non Repetitive Surge Peak On-state Current	10ms, T _j =25°C	1100	
I ² t	For Fusing	10ms, T _j =25°C	6050	A ² S
V _{TM}	Peak on-state voltage	I _{TM} =150A	1.7	V
dv/dt	critical rate of rise of off-state voltage	V _D =2/3V _{DRM} Gate Open T _j =125°C	1000	V/us
I _{GT}	gate trigger current max.		80	mA
V _{GT}	gate trigger voltage max.		1.5	V
I _H	gate trigger current		200	mA
I _L	latching current		500	mA
Viso	AC 50Hz RMS 1min		2500	V
T _J	Junction Temperature		-40 to +125	°C
T _{STG}	Storage Temperature Range		-40 to +125	
R _{thJC}	Junction to Case Thermal Resistance(Per thyristor chip)		0.7	°C /W
Torque	mounting force, Module to Sink		2.5	Nm
Tsolder	Teminals,10s		260	°C

Outlines

